

## TO-92S Plastic-Encapsulate Transistors

### KTA1297 TRANSISTOR (PNP)

#### FEATURES

- General Purpose Switching Application

#### MAXIMUM RATINGS ( $T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	-20	V
$V_{CEO}$	Collector-Emitter Voltage	-20	V
$V_{EBO}$	Emitter-Base Voltage	-6	V
$I_C$	Collector Current	-2	A
$P_C$	Collector Power Dissipation	400	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	312	$^{\circ}\text{C}/\text{W}$
$T_j$	Junction Temperature	150	$^{\circ}\text{C}$
$T_{stg}$	Storage Temperature	-55~+150	$^{\circ}\text{C}$

#### TO - 92S

1. EMITTER
2. COLLECTOR
3. BASE



#### ELECTRICAL CHARACTERISTICS ( $T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -0.1\text{mA}, I_E = 0$	-20			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}, I_B = 0$	-20			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -0.1\text{mA}, I_C = 0$	-6			V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -20\text{V}, I_E = 0$			-0.1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -6\text{V}, I_C = 0$			-0.1	$\mu\text{A}$
DC current gain	$h_{FE(1)}$	$V_{CE} = -2\text{V}, I_C = -0.1\text{A}$	120		400	
	$h_{FE(2)}$	$V_{CE} = -2\text{V}, I_C = -2\text{A}$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -2\text{A}, I_B = -0.1\text{A}$			-0.5	V
Base-emitter voltage	$V_{BE}$	$V_{CE} = -2\text{V}, I_C = -0.1\text{A}$			-0.85	V
Collector output capacitance	$C_{ob}$	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$		40		pF
Transition frequency	$f_T$	$V_{CE} = -2\text{V}, I_C = -0.5\text{A}$		120		MHz

#### CLASSIFICATION OF $h_{FE(1)}$

RANK	Y	GR
RANGE	120-240	200-400